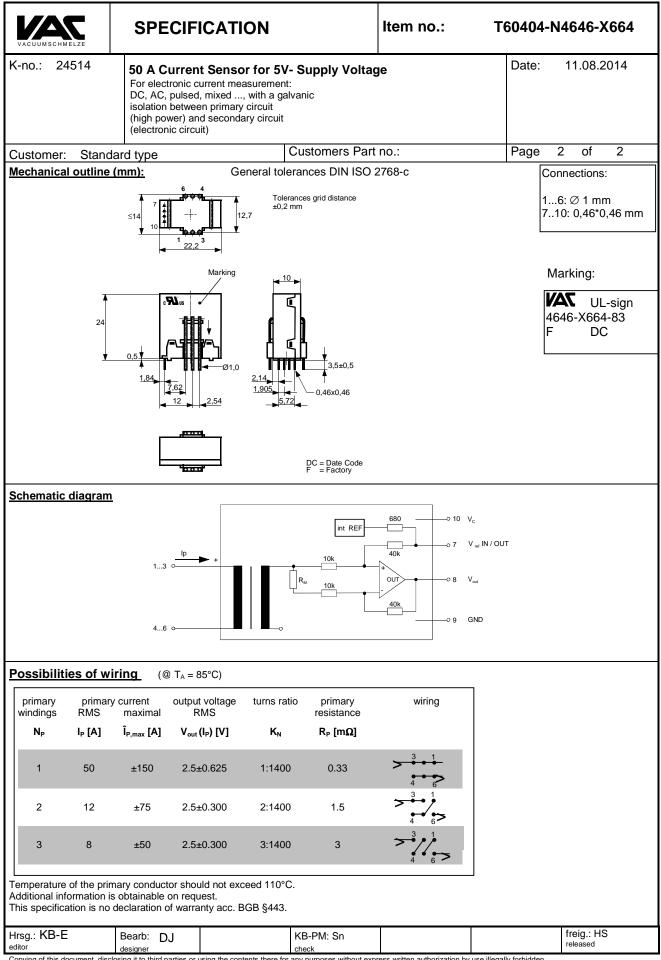
VACUUMSCHMELZE	SPECIFICATION	Item no.:	T60404-N4	646-X664
۲-no.: 24514	50 A Current Sensor for 5V- Supply For electronic current measurement: DC, AC, pulsed, mixed, with a galvanic isolation between primary circuit (high power) and secondary circuit (electronic circuit)	Voltage	Date:	11.08.2014
Customer: Stand	dard type Customer	rs Part no.:	Page 1	of 2
Description Closed loop (compe Current Sensor with field probe Printed circuit board Casing and materia	Characteristics ensation) • Excellent accuracy n magnetic • Very low offset current of mounting • Very low temperature depender	Applications Mainly used fo applications: ncy and offset • AC variate drives rrent • Static cor • Battery su • Switched • Power Su	-	on in industrial d servo motor or drives lies (SMPS) applications
Electrical data – Ra		50		۸
I _{PN}	Primary nominal r.m.s. current	50) _{Ref} ± (0.625*I _P /I _{PN})	A V
V _{out}	Output voltage @ I _P			V
V _{out} V _{Ref}	Output voltage @ I _P =0, T _A =25°C External Reference voltage range		Ref ± 0.000725	V
V Ref	Internal Reference voltage	-	+ .5 ±0.005	V
K _N	Turns ratio		3 : 1400	v
I NN				
<u> Accuracy – Dynam</u>	ic performance data	min. typ.	max.	Unit
I _{P,max}	Max. measuring range	±150	max.	Unit
X	Accuracy @ I _{PN} , T _A = 25°C		0.7	%
ε∟	Linearity		0.1	%
V _{out} - V _{Ref}	Offset voltage @ I _P =0, T _A = 25°C		±0.725	mV
Δ V _o / V _{Ref} / Δ T	Temperature drift of Vout @ IP=0, VRef =2,5V	/, T _A = -4085°C 0.7	7	ppm/°C
t _r	Response time @ 90% von I _{PN}	300		ns
∆t (I _{P,max})	Delay time at di/dt = 100 A/ μ s	200		ns
f	Frequency bandwidth	DC200		kHz
Seneral data				
		min. typ.	max.	Unit
T _A	Ambient operating temperature	-40	+85	°C
Ts	Ambient storage temperature	-40	+85	°C
m	Mass	12		g
Vc	Supply voltage	4.75 5	5.25	V
I _C	Current consumption	15		mA
	Constructed and manufactored and tested i Reinforced insulation, Insulation material gr)-5-1 (Pin 1 - 6 to F	Pin 7 – 10)
S _{clear}	Clearance (component without solder pad)	7.4		mm
Screep	Creepage (component without solder pad)	8.0 DMC	200	mm
V	System voltageovervoltage category 3Working voltage(tabel 7 acc. to EN6180	RMS	300	V
V _{sys} Vwork		RMS	650	V
V _{sys} V _{work}	overvoltage category 2	IXIVIO		
	overvoltage category 2 Rated discharge voltage	peak value	1320	V
V _{work} U _{PD}	Rated discharge voltage			
V _{work} U _{PD}	v v <i>i</i>	peak value	1320	V V _{AC}
V _{work} U _{PD} Max. potential di	Rated discharge voltage	peak value	1320	
V _{work} U _{PD} Max. potential di	Rated discharge voltage	peak value RMS	1320 600	V _{AC}
V _{work} U _{PD} Max. potential di Date Name Is	Rated discharge voltage	peak value RMS	1320 600	V _{AC}

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VACUUMSCHMELZE	Additional Information	Item No.:	Г60404-N464	6-X664
No.: 24514	50 A Current Sensor for 5V- Supp For the electronic measurement of currents: DC, AC, pulsed, mixed, with a galvanic Isolation between the primary circuit (high power) and the secondary circuit	bly Voltage	Date:	11.08.2014
ustomer:	Custome	ers Part No.:	Page 1	of 2
ectrical Data				11
V _{Ctot}	Maximum supply voltage (without function)	<mark>min. typ.</mark>	max. 7	Unit V
lc	Supply Current with primary current	15mA +lp*K _N +V _c	ut/RL	mA
lout,SC	Short circuit output current	±20		mA
R _P	Resistance / primary winding @ T _A =25°C	1		mΩ
Rs	Secondary coil resistance @ T _A =85°C		35	Ω
R _{i,Ref}	Internal resistance of Reference input	670		Ω
R _i ,(V _{out})	Output resistance of Vout		1	Ω
RL	External recommended resistance of V_{out}	1		kΩ
CL	External recommended capacitance of Vout		500	pF
ΔΧ _{ΤΙ} / ΔΤ	Temperature drift of X @ $T_A = -40 \dots +85 \circ C$		40	ppm/K
$\Delta V_0 = \Delta (V_{out} - V_{Ref})$	Sum of any offset drift including:	2	6	mV
V _{0t}	Longtermdrift of V ₀	1		mV
V _{0T}	Temperature drift von V ₀ @ T _A = -40+85			mV
V _{0H}	Hysteresis of V _{out} @ I _P =0 (after an overload of	of 10 x I _{PN})	1	mV
$\Delta V_0 / \Delta V_C$	Supply voltage rejection ratio		1	mV/V
V _{oss}	Offsetripple (with 1 MHz- filter first order)		35	mV
V _{oss}	Offsetripple (with 100 kHz- filter firdt order)	2	5	mV
V _{oss}	Offsetripple (with 20 kHz- filter first order)	0.6	1	mV
				۳ ۲
k	Maximum possible coupling capacity (prima Mechanical stress according to M3209/3 Settings: 10 – 2000 Hz, 1 min/Octave, 2 hc		10 30g	pF
<u>ispection</u> (Measu V _{out} (SC) ([\]	Mechanical stress according to M3209/3 Settings: 10 – 2000 Hz, 1 min/Octave, 2 hc rement after temperature balance of the samples at 1 V) M3011/6: Output voltage vs. external ref	ours room temperature), SC = signifi	10 30g cant characteristi 625±0,7%	c mV
<u>spection</u> (Measu V _{out} (SC) (\ V _{out} –V _{Ref} (I _P =0) (\	Mechanical stress according to M3209/3 Settings: 10 – 2000 Hz, 1 min/Octave, 2 hc rement after temperature balance of the samples at a V) M3011/6: Output voltage vs. external ref V) M3226: Offset voltage	ours room temperature), SC = signifi	10 30g cant characteristi 625±0,7% ± 0.725	c mV mV
<u>spection</u> (Measu V _{out} (SC) (\ V _{out} –V _{Ref} (I _P =0) (\ V _d (\	Mechanical stress according to M3209/3 Settings: 10 – 2000 Hz, 1 min/Octave, 2 hc rement after temperature balance of the samples at 1 V) M3011/6: Output voltage vs. external ref V) M3226: Offset voltage V) M3014: Test voltage, rms, 1 s pin 1 – 6 vs. pin 7 – 10	ours room temperature), SC = signifi erence (I _P =3x10As, 40-80Hz)	10 $30g$ cant characteristi $625\pm0,7\%$ ± 0.725 1.5	c mV mV kV
I <mark>spection</mark> (Measu V _{out} (SC) (\ V _{out} –V _{Ref} (I _P =0) (\ V _d (\	Mechanical stress according to M3209/3 Settings: 10 – 2000 Hz, 1 min/Octave, 2 hc rement after temperature balance of the samples at a V) M3011/6: Output voltage vs. external ref V) M3226: Offset voltage V) M3014: Test voltage, rms, 1 s	ours room temperature), SC = signifi erence (I _P =3x10As, 40-80Hz)	10 30g cant characteristi 625±0,7% ± 0.725	c mV mV
<mark>Nspection</mark> (Measu V _{out} (SC) (N V _{out} –V _{Ref} (Ip=0) (N V _d (N V _e (A	Mechanical stress according to M3209/3 Settings: 10 – 2000 Hz, 1 min/Octave, 2 hc rement after temperature balance of the samples at 1 V) M3011/6: Output voltage vs. external ref V) M3226: Offset voltage V) M3014: Test voltage, rms, 1 s pin 1 – 6 vs. pin 7 – 10 AQL 1/S4) Partial discharge voltage acc.N with V _{vor} (RMS)	ours room temperature), SC = signifi erence (I _P =3x10As, 40-80Hz)	10 30g cant characteristi $625\pm0,7\%$ ± 0.725 1.5 1400	c mV mV kV
n <u>spection</u> (Measu V _{out} (SC) (\ V _{out} –V _{Ref} (I _P =0) (\ V _d (\ V _e (<i>A</i> V _e (<i>A</i>	Mechanical stress according to M3209/3 Settings: 10 – 2000 Hz, 1 min/Octave, 2 hc rement after temperature balance of the samples at 1 V) M3011/6: Output voltage vs. external ref V) M3226: Offset voltage V) M3014: Test voltage, rms, 1 s pin 1 – 6 vs. pin 7 – 10 AQL 1/S4) Partial discharge voltage acc.N with V _{vor} (RMS)	ours room temperature), SC = signifi erence (I _P =3x10As, 40-80Hz) M3024 (RMS)	10 30g cant characteristi $625\pm0,7\%$ ± 0.725 1.5 1400	c mV mV kV
N <mark>spection</mark> (Measu V _{out} (SC) (\ V _{out} –V _{Ref} (I _P =0) (\ V _d (\ V _e (<i>I</i> V _e (<i>I</i> V _e (<i>I</i> V _w V _d (Pin V _w V _d	Mechanical stress according to M3209/3 Settings: 10 – 2000 Hz, 1 min/Octave, 2 hc rement after temperature balance of the samples at 1 V) M3011/6: Output voltage vs. external ref V) M3226: Offset voltage V) M3014: Test voltage, rms, 1 s pin 1 – 6 vs. pin 7 – 10 AQL 1/S4) Partial discharge voltage acc.N with V _{vor} (RMS) 1 - 6 to Pin 7 - 10) HV transient test according to M3064 (1,2) Testing voltage to M3014	purs room temperature), SC = signifi erence (I _P =3x10As, 40-80Hz) M3024 (RMS) us / 50 μs-wave form) (5 s)	10 30g cant characteristi 625±0,7% ± 0.725 1.5 1400 1750 8 3	c mV kV V V V
I <mark>spection</mark> (Measu V _{out} (SC) (\ V _{out} -V _{Ref} (I _P =0) (\ V _d (\ V _e (<i>I</i> V _e (<i>I</i> V _e (<i>I</i> V <u>v</u> V <u>v</u> (Pin V _w V _d	Mechanical stress according to M3209/3 Settings: 10 – 2000 Hz, 1 min/Octave, 2 hc rement after temperature balance of the samples at 1 V) M3011/6: Output voltage vs. external ref V) M3226: Offset voltage V) M3014: Test voltage, rms, 1 s pin 1 – 6 vs. pin 7 – 10 AQL 1/S4) Partial discharge voltage acc.N with V _{vor} (RMS) 1 - 6 to Pin 7 - 10) HV transient test according to M3064 (1,2) Testing voltage to M3014 Partial discharge voltage acc.M3024 (RMS)	purs room temperature), SC = signifi erence (I _P =3x10As, 40-80Hz) M3024 (RMS) us / 50 μs-wave form) (5 s)	10 30g cant characteristi 625±0,7% ± 0.725 1.5 1400 1750 8 3 1400	c mV kV V V V
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Aspection (Measu V _{out} (SC) (' V _{out} -V _{Ref} (I _P =0) (' V _d (' V _e (<i>A</i> V _e (<i>A</i> V _e V _d V _d V _d V _e Pplicable docum	Mechanical stress according to M3209/3 Settings: 10 – 2000 Hz, 1 min/Octave, 2 hc rement after temperature balance of the samples at 1 V) M3011/6: Output voltage vs. external ref V) M3226: Offset voltage V) M3014: Test voltage, rms, 1 s pin 1 – 6 vs. pin 7 – 10 AQL 1/S4) Partial discharge voltage acc.N with V _{vor} (RMS) 1 - 6 to Pin 7 - 10) HV transient test according to M3064 (1,2 p Testing voltage to M3014 Partial discharge voltage acc.M3024 (RMS with V _{vor} (RMS)	purs room temperature), SC = signifi erence (I _P =3x10As, 40-80Hz) M3024 (RMS) us / 50 μs-wave form) (5 s)	10 30g cant characteristi $625\pm0,7\%$ ± 0.725 1.5 1400 1750 8 3 1400 1750	c mV kV V V V
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Aspection (Measu Vout (SC) (N Vout—VRef (IP=0) (N Vd (N Ve (A Ye (A	Mechanical stress according to M3209/3 Settings: 10 – 2000 Hz, 1 min/Octave, 2 hc rement after temperature balance of the samples at 1 V) M3011/6: Output voltage vs. external ref V) M3226: Offset voltage V) M3014: Test voltage, rms, 1 s pin 1 – 6 vs. pin 7 – 10 AQL 1/S4) Partial discharge voltage acc.N with V _{vor} (RMS) 1 - 6 to Pin 7 - 10) HV transient test according to M3064 (1,2 p Testing voltage to M3014 Partial discharge voltage acc.M3024 (RMS with V _{vor} (RMS) ents positive output current appears at point V _{out} , by primary to IEC529: IP50.	purs room temperature), SC = signifi erence (I _P =3x10As, 40-80Hz) M3024 (RMS) us / 50 μs-wave form) (5 s)	10 30g cant characteristi $625\pm0,7\%$ ± 0.725 1.5 1400 1750 8 3 1400 1750	c mV kV V V V
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tr: Res at IF Δt (I _{Pmax}): Dela mea UPD Ratec UPD Ratec UPD Vvor Define Vvor Define Vvor Syste Vvor Vsys Syste Vwork Worki Vo: Offs Vo= VoH: Zero VoH: Zero Xi: Pern X xges(IPN): Pern			0404-N4646-X664
Explanation of tr: Res at IF Δt (IPmax): Dela mea UPD Ratec UPD Ratec UPD Vvor Define test in Vvor Vsys Syste Vwork Worki Vor: Offs Vor: Offs Vor: Zerc Vor: Lon X: Pern X ges(IPN): Pern	50 A Current Sensor for 5V- Supp For the electronic measurement of currents: DC, AC, pulsed, mixed, with a galvanic Isolation between the primary circuit (high power) and the secondary circuit	ly Voltage	Date: 11.08.2014
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mea UPD Ratec UPD Ratec UPD Vvor Defind test in Vvor Vsys Syste Vwork Worki Vo: Offs Vo= VoH: Zerd VoH: Zerd VoH: Lon X: Pern X ges(IPN): Pern	Response time (describe the dynamic performance for at $I_P = 0.9$ $^{\circ}$ I_{PN} between a rectangular current and the		nge), measured as delay time
UPD Vvor Define test in Vvor Vsys Syste Vwork Worki Vo: Offs Vo= Voh: Zero Voh: Lon X: Pern X ges(IPN): Pern X _{ges}	Delay time (describe the dynamic performance for the measured between I_{Pmax} and the output voltage $V_{\text{out}}(I_{\text{P}}$		-
test ir V _{vor} V _{sys} Syste V _{work} Worki V ₀ : Offs V ₀ : Zero V ₀ : Lon X: Pern X X _{ges} (I _{PN}): Pern X _{ges}	Rated discharge voltage (recurring peak voltage separated J_{PD} = $\sqrt{2} * V_e / 1,5$	ted by the insulation) proved wi	th a sinusoidal voltage $V_{\rm e}$
V _{sys} Syste V _{work} Worki V ₀ : Offs V ₀ : Zero V ₀₁ : Lon X: Pern X X _{ges} (I _{PN}): Pern X _{ges}	Defined voltage is the RMS valve of a sinusoidal voltage est in IEC 61800-5-1	e with peak value of 1,875 * U _{PC}	o required for partial discharg
V _{work} Worki V ₀ : Offs V ₀ : Zerc V ₀ I: Lon X: Pern X X _{ges} (I _{PN}): Pern X _{ges}	$v_{\rm vor} = 1,875 {}^*{\rm U}_{\rm PD} / \sqrt{2}$		
V ₀ : Offs V ₀ : Zero V ₀₁ : Lon X: Pern X X _{ges} (I _{PN}): Pern X _{ges}	system voltage RMS value of rated voltage according	ng to IEC 61800-5-1	
Vo= VoH: Zerr Vot: Lon X: Perr X Xges(IPN): Perr X _{ges}	Vorking voltage voltage according to IEC 61800-5-1	which occurs by design in a cir	cuit or across insulation
V _{0t} : Lon X: Perr X X _{ges} (I _{PN}): Perr X _{ges}	Offset voltage between V _{out} and the rated reference voltage V _o = V _{out} (0) - 2,5V	bltage of $V_{ref} = 2,5V.$	
X: Peri X X _{ges} (I _{PN}): Peri X _{ge}	Zero variation of $V_{\mbox{\scriptsize o}}$ after overloading with a DC of tenform	old the rated value	
X X _{ges} (I _{PN}): Peri X _{ge}	Long term drift of V_o after 100 temperature cycles in th	ne range -40 bis 85 °C.	
X _{ges} (I _{PN}): Peri X _{ge}	Permissible measurement error in the final inspection at $X = 100 \cdot \left \frac{V_{out}(I_{PN}) - V_{out}(0)}{0.625 V} - 1 \right \%$	at RT, defined by	
X _{ge}	$X = 100 \cdot \left \frac{-0.01 - 11}{0,625 \text{V}} - 1 \right \%$		
ε _L : Line	$ \begin{array}{l} \text{Permissible measurement error including any drifts over } \\ X_{\text{ges}} = 100 \cdot \left \frac{V_{\text{out}} \left(I_{\text{PN}} \right) - 2.5V}{0.625V} - 1 \right \text{\% or} X_{\text{ges}} = 100 \cdot \left \frac{V_{\text{out}} \left(I_{\text{PN}} \right) - 2.5V}{0.625V} - 1 \right \text{\% or} X_{\text{ges}} = 100 \cdot \left \frac{V_{\text{out}} \left(I_{\text{PN}} \right) - 2.5V}{0.625V} - 1 \right \text{\% or} X_{\text{ges}} = 100 \cdot \left \frac{V_{\text{out}} \left(I_{\text{PN}} \right) - 2.5V}{0.625V} - 1 \right \text{\% or} X_{\text{ges}} = 100 \cdot \left \frac{V_{\text{out}} \left(I_{\text{PN}} \right) - 2.5V}{0.625V} - 1 \right \text{\% or} X_{\text{ges}} = 100 \cdot \left \frac{V_{\text{out}} \left(I_{\text{PN}} \right) - 2.5V}{0.625V} - 1 \right \text{\% or} X_{\text{ges}} = 100 \cdot \left \frac{V_{\text{out}} \left(I_{\text{PN}} \right) - 2.5V}{0.625V} - 1 \right \text{\% or} X_{\text{ges}} = 100 \cdot \left \frac{V_{\text{out}} \left(I_{\text{PN}} \right) - 2.5V}{0.625V} - 1 \right \text{\% or} X_{\text{ges}} = 100 \cdot \left \frac{V_{\text{out}} \left(I_{\text{PN}} \right) - 2.5V}{0.625V} - 1 \right \text{\% or} X_{\text{ges}} = 100 \cdot \left \frac{V_{\text{out}} \left(I_{\text{PN}} \right) - 2.5V}{0.625V} - 1 \right \text{\% or} X_{\text{ges}} = 100 \cdot \left \frac{V_{\text{out}} \left(I_{\text{PN}} \right) - 2.5V}{0.625V} - 1 \right \text{\% or} X_{\text{ges}} = 100 \cdot \left \frac{V_{\text{out}} \left(I_{\text{PN}} \right) - 2.5V}{0.625V} - 1 \right \text{\% or} X_{\text{ges}} = 100 \cdot \left \frac{V_{\text{out}} \left(I_{\text{PN}} \right) - 2.5V}{0.625V} - 1 \right \text{\% or} X_{\text{ges}} = 100 \cdot \left \frac{V_{\text{out}} \left(I_{\text{PN}} \right) - 2.5V}{0.625V} - 1 \right \text{\% or} X_{\text{ges}} = 100 \cdot \left \frac{V_{\text{out}} \left(I_{\text{PN}} \right) - 2.5V}{0.625V} - 1 \right \text{\% or} X_{\text{ges}} = 100 \cdot \left \frac{V_{\text{out}} \left(I_{\text{PN}} \right) - 2.5V}{0.65V} - 1 \right \text{\% or} X_{\text{ges}} = 100 \cdot \left \frac{V_{\text{out}} \left(I_{\text{PN}} \right) - 2.5V}{0.65V} - 1 \right \text{\% or} X_{\text{ges}} = 100 \cdot \left \frac{V_{\text{out}} \left(I_{\text{PN}} \right) - 2.5V}{0.65V} - 1 \right \text{\% or} X_{\text{ges}} = 100 \cdot \left \frac{V_{\text{out}} \left(I_{\text{PN}} \right) - 2.5V}{0.65V} - 1 \right X_{\text{ges}} = 100 \cdot 1$		
	Linearity fault defined by $\mathcal{E}_{\rm L} = 100 \cdot \left \frac{I_{\rm P}}{I_{\rm PN}} - \frac{V_{out}}{V_{out}} \right $	$\frac{(I_P) - V_{out}(0)}{(I_{PN}) - V_{out}(0)} \bigg \%$	
This "Additional	onal information" is no declaration of warranty according	g BGB §443.	
Hrsg.: KB-E			

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